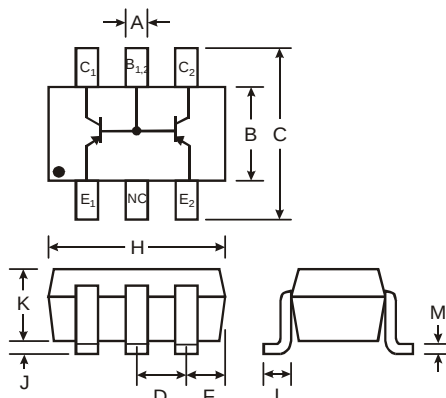


Features

- Epitaxial Planar Die Construction
- Intrinsically Matched PNP Pair (Note 1)
- Small Surface Mount Package
- 2% h_{FE} Matched Tolerance
- **Lead Free/RoHS Compliant (Note 3)**
- **"Green" Device (Note 4 and 5)**

Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound, Note 5. UL Flammability Classification Rating 94V-0
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Copper leadframe).
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.015 grams (approximate)



SOT-26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
F	—	—	0.55
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
All Dimensions in mm			

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-200	mA
Power Dissipation (Note 2)	P_d	225	mW
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
1. Built with adjacent die from a single wafer.
 2. Device mounted on FR5 PCB: 1.0 x 0.75 x 0.62 in.; pad layout as shown on suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 3. No purposefully added lead.
 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 5. Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-40	—	V	I _C = -10μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-40	—	V	I _C = -1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5.0	—	V	I _E = -10μA, I _C = 0
Collector Cutoff Current	I _{CEX}	—	-50	nA	V _{CE} = -30V, V _{EB(OFF)} = -3.0V
Base Cutoff Current	I _{BL}	—	-50	nA	V _{CE} = -30V, V _{EB(OFF)} = -3.0V
ON CHARACTERISTICS (Note 6)					
DC Current Gain (Note 7)	h _{FE}	60	—	—	I _C = -100μA, V _{CE} = -1.0V
		80	—		I _C = -1.0mA, V _{CE} = -1.0V
		100	300		I _C = -10mA, V _{CE} = -1.0V
		60	—		I _C = -50mA, V _{CE} = -1.0V
		30	—		I _C = -100mA, V _{CE} = -1.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	-0.25 -0.40	V	I _C = -10mA, I _B = -1.0mA I _C = -50mA, I _B = -5.0mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	-0.65 —	-0.85 -0.95	V	I _C = -10mA, I _B = -1.0mA I _C = -50mA, I _B = -5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	4.5	pF	V _{CB} = -5.0V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{ibo}	—	10	pF	V _{EB} = -0.5V, f = 1.0MHz, I _C = 0
Input Impedance	h _{ie}	2.0	12	kΩ	V _{CE} = 10V, I _C = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h _{re}	0.1	10	x 10 ⁻⁴	
Small Signal Current Gain	h _{fe}	100	400	—	
Output Admittance	h _{oe}	3.0	60	μS	V _{CE} = -20V, I _C = -10mA, f = 100MHz
Current Gain-Bandwidth Product	f _T	250	—	MHz	
Noise Figure	NF	—	4.0	dB	V _{CE} = -5.0V, I _C = -100μA, R _S = 1.0kΩ, f = 1.0kHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	—	35	ns	V _{CC} = -3.0V, I _C = -10mA, V _{BE(off)} = 0.5V, I _{B1} = -1.0mA
Rise Time	t _r	—	35	ns	
Storage Time	t _s	—	225	ns	V _{CC} = -3.0V, I _C = -10mA, I _{B1} = I _{B2} = -1.0mA
Fall Time	t _f	—	75	ns	

- Notes: 6. Short duration pulse test used to minimize self-heating effect.
7. The DC current gain, h_{FE}, is matched at I_C = -10mA and V_{CE} = -1.0V with typical matched tolerances of 1% and maximum of 2%.

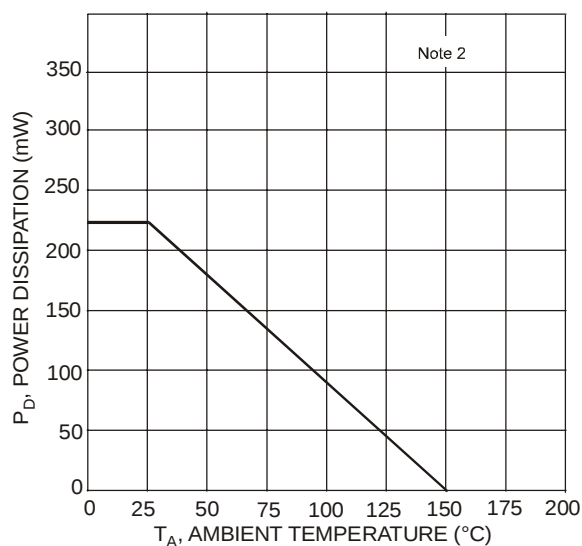


Fig. 1, Max Power Dissipation vs. Ambient Temperature, Total Device

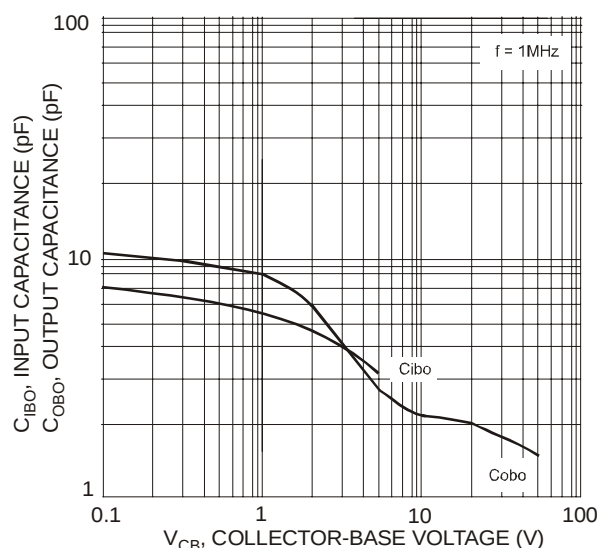


Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage

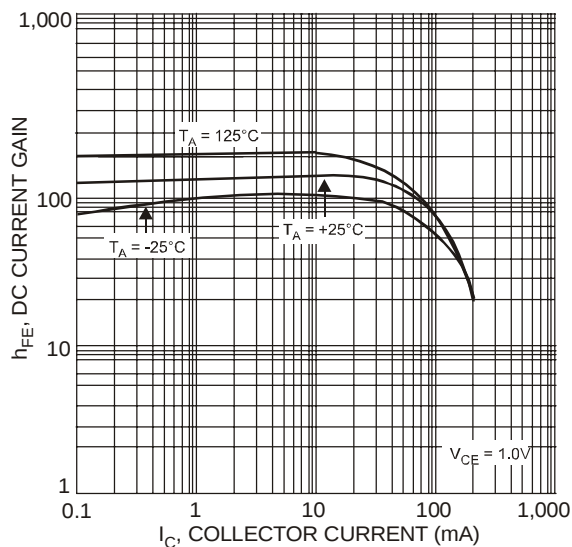


Fig. 3, Typical DC Current Gain vs. Collector Current

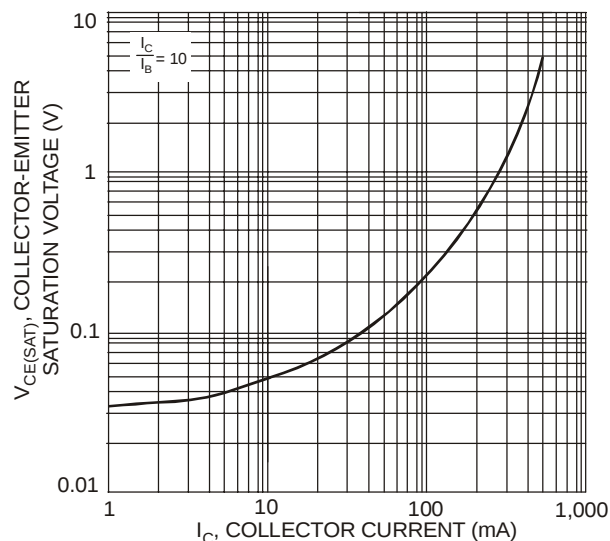


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

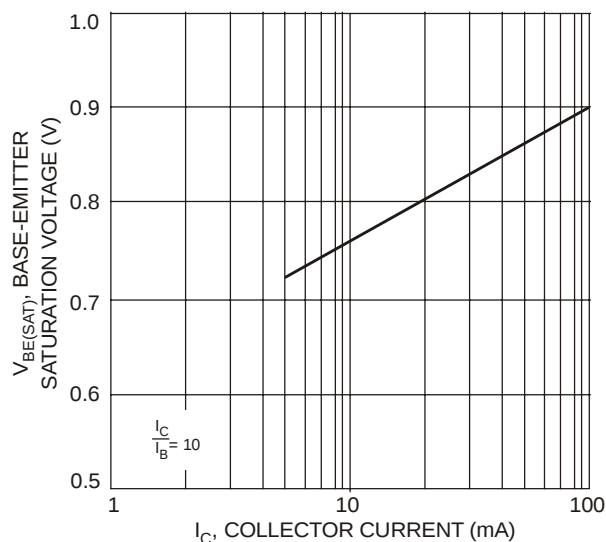


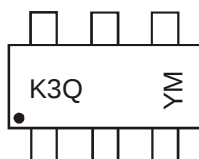
Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current

Ordering Information (Note 5 & 8)

Device	Packaging	Shipping
DMMT3906-7-F	SOT-26	3000/Tape & Reel

Notes: 8. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



K3Q = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: T = 2006
 M = Month ex: 9 = September

Date Code Key

Year	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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